

Product Summary

$V_{(BR)CES}$	$V_{CE(SAT)MAX}$	$I_c(100^\circ C)$
650V	1.8V@15V	60A

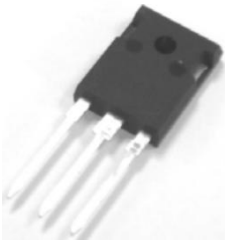
Feature

- High speed smooth switching device for hard & soft switching
- Positive temperature coefficient
- High ruggedness, temperature stable

Application

- Solar converters
- Welding converters
- Mid to high range switching frequency converters
- Uninterruptible power supply

Package

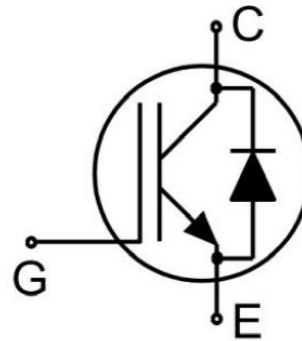


TO-247AB

Marking



Circuit diagram



Absolute maximum ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEs}	650	V
Continuous Gate- Emitter Voltage	V _{GES}	±20	V
Collector Current	I _c	80	A
Collector Current(T _C =100°C)	I _c (100°C)	60	A
Pulsed Collector Current, tp limited by T _{jmax} ,V _{GE} =15V	I _{CM}	240	A
Diode Continuous Forward Current	I _F	80	A
Diode Continuous Forward Current(T _C =100°C)	I _F (100°C)	60	A
Diode Forward Pulsed Current,tp limited by T _{jmax}	I _{Fpuls}	240	A
Turn off Safe Operating Area V _{CE} ≤650V,T _J ≤150°C	-	240	A
Power Dissipation(T _J =175°C)	P _D	283	W
Thermal Resistance, Junction to case for Diode	R _{θJC}	1.05	°C/W
Thermal Resistance, Junction to case for IGBT	R _{θJC}	0.53	°C/W
Maximum Temperature for Soldering,wave soldering 1.6mm (0.063in.) from case for 10s	T _L	260	°C
Junction Temperature Range	T _J	-40 ~ +175	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical characteristics of the IGBT (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	V _{GE} = 0V, I _{CE} =250uA	650			V
Collector-Emitter Leakage Current	I _{CEs}	V _{GE} = 0V, V _{CE} =650V			0.25	mA
		V _{GE} = 0V, V _{CE} =650V, T _J =150°C			3	
Gate to Emitter Leakage Current	I _{GES}	V _{GE} =±20V, V _{CE} = 0V			100	nA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V, I _c =60A,	1.20	1.50	1.80	V
		V _{GE} =15V, I _c =60A, T _J =125°C		1.70		
		V _{GE} =15V, I _c =60A, T _J =150°C		1.80		
Gate Threshold Voltage	V _{GE(th)}	V _{CE} =V _{GE} , I _c =0.5mA	3.0	4.0	5.0	V
Dynamic characteristics						
Input Capacitance	C _{ies}	V _{CE} =25V, V _{GE} =0V, f =1MHz		2.86		nF
Reverse Transfer Capacitance	C _{res}			0.02		nF
Total Gate Charge	Q _g	V _{CC} =520V, V _{GE} =15V, I _c =60A		0.18		uC
Turn-on delay time	t _{d(on)}	V _{CC} =400V, V _{GE} = -5V~15V, I _c =60A, R _G =10Ω, Inductive Load, T _J =25°C		27		nS
Turn-on rise time	t _r			41		
Turn-off delay time	t _{d(off)}			81		
Turn-off fall time	t _f			45		mJ
Turn-on Switching energy	E _{on}			2.47		
Turn-off Switching energy	E _{off}			0.67		
Total Switching energy	E _{ts}		3.14			
Turn-on delay time	t _{d(on)}	V _{CC} =400V, V _{GE} = -5V~15V, I _c =60A, R _G =10Ω, Inductive Load, T _J =125°C		28		nS
Turn-on rise time	t _r			49		
Turn-off delay time	t _{d(off)}			88		
Turn-off fall time	t _f			57		mJ
Turn-on Switching energy	E _{on}			2.53		
Turn-off Switching energy	E _{off}			0.89		
Total Switching energy	E _{ts}		3.42			
Turn-on delay time	t _{d(on)}	V _{CC} =400V, V _{GE} = -5V~15V, I _c =60A, R _G =10Ω, Inductive Load, T _J =150°C		29		nS
Turn-on rise time	t _r			52		
Turn-off delay time	t _{d(off)}			93		
Turn-off fall time	t _f			66		mJ
Turn-on Switching energy	E _{on}			2.57		
Turn-off Switching energy	E _{off}			0.93		
Total Switching energy	E _{ts}		3.50			

Electrical characteristics of the Diode ($T_j=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Diode Forward Voltage	V_F	$I_F=60\text{A}$		1.70	2.10	V
		$I_F=60\text{A}, T_j=125^\circ\text{C}$		1.60		
		$I_F=60\text{A}, T_j=150^\circ\text{C}$		1.50		
Reverse Recovery Current	I_{rr}	$I_F=60\text{A}, V_R=400\text{V}, -di/dt=460\text{A}/\mu\text{s}$		16		A
Diode reverse recovery time	t_{rr}			155		ns
Reverse Recovery Charge	Q_{rr}			1.76		μC
Reverse recovery energy	E_{rec}			0.34		mJ
Reverse Recovery Current	I_{rr}	$I_F=60\text{A}, V_R=400\text{V}, -di/dt=460\text{A}/\mu\text{s}, T_j=125^\circ\text{C}$		22		A
Diode reverse recovery time	t_{rr}			196		ns
Reverse Recovery Charge	Q_{rr}			2.83		μC
Reverse recovery energy	E_{rec}			0.71		mJ
Reverse Recovery Current	I_{rr}	$I_F=60\text{A}, V_R=400\text{V}, -di/dt=460\text{A}/\mu\text{s}, T_j=150^\circ\text{C}$		25		A
Diode reverse recovery time	t_{rr}			227		ns
Reverse Recovery Charge	Q_{rr}			3.66		μC
Reverse recovery energy	E_{rec}			0.85		mJ

Typical Characteristics

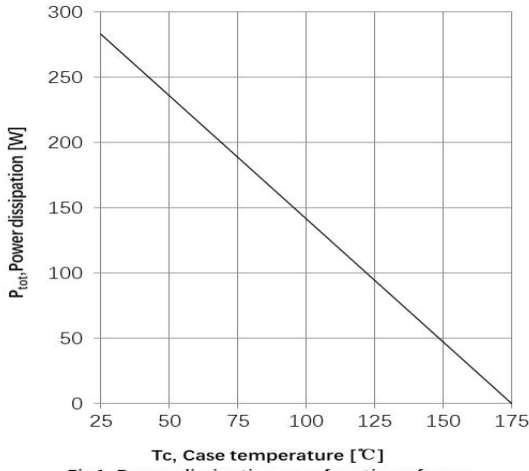


Fig1. Power dissipation as a function of case temperature ($T_j \leq 175^\circ\text{C}$)

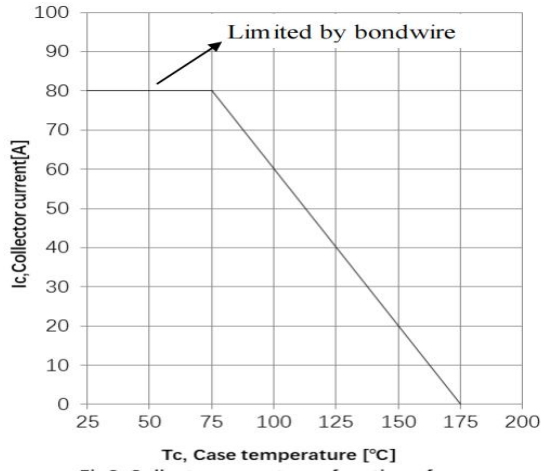


Fig2. Collector current as a function of case temperature ($V_{ge} \geq 15\text{V}$, $T_j \leq 175^\circ\text{C}$)

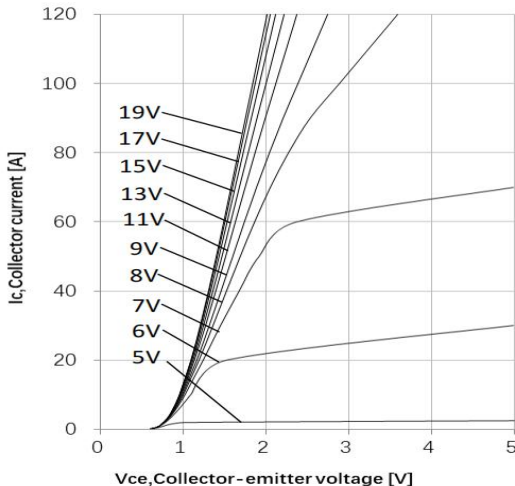


Fig3. Typical output characteristic ($T_j = 25^\circ\text{C}$)

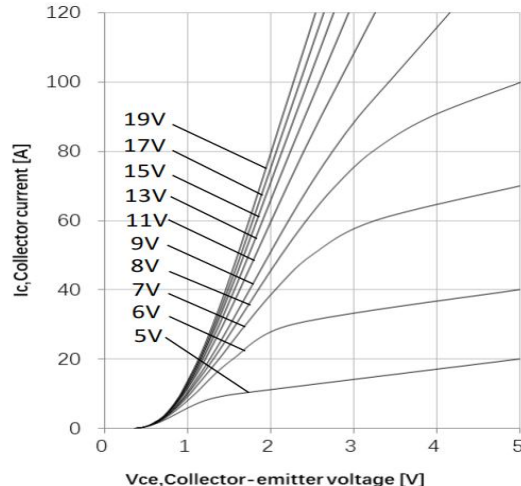


Fig4. Typical output characteristic ($T_j = 150^\circ\text{C}$)

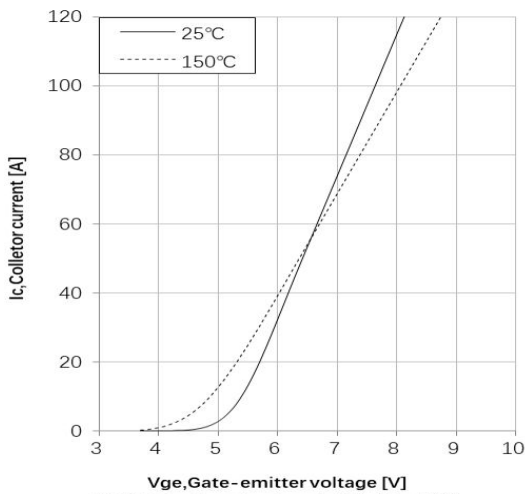


Fig5. Typical transfer characteristic ($V_{ce} = 20\text{V}$)

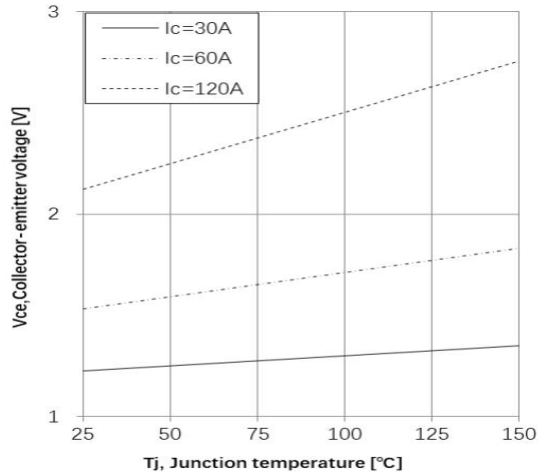
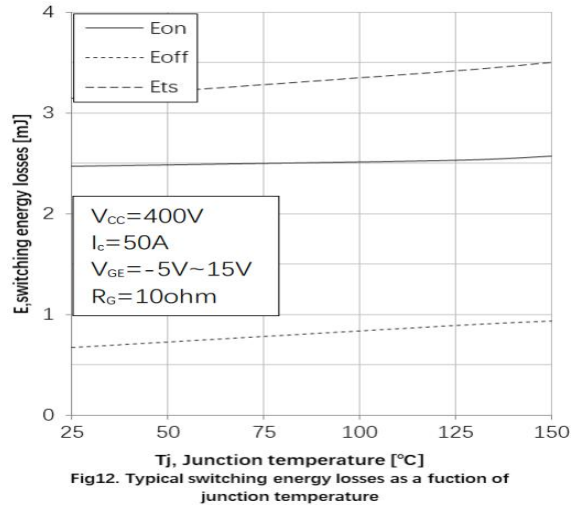
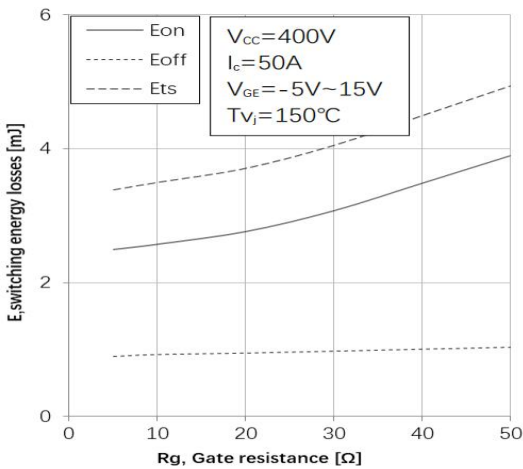
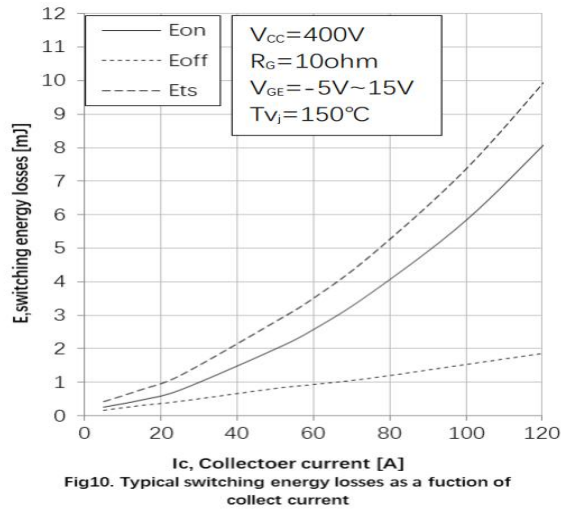
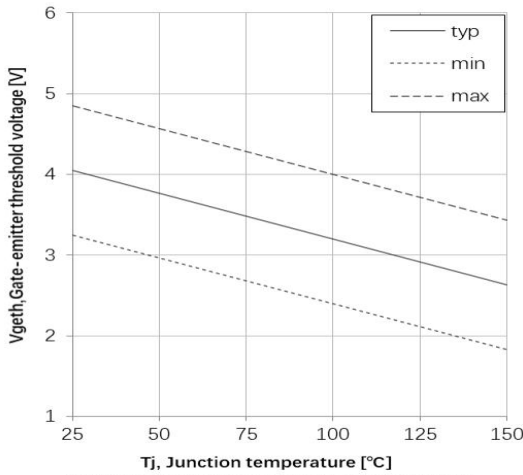
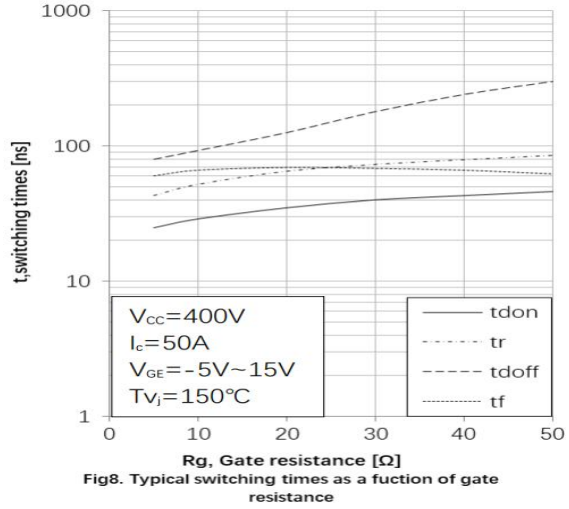
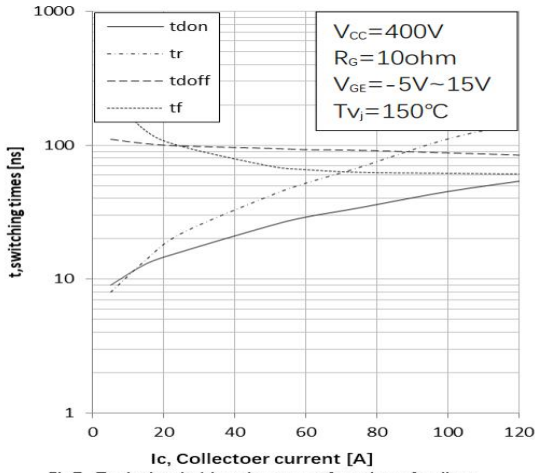
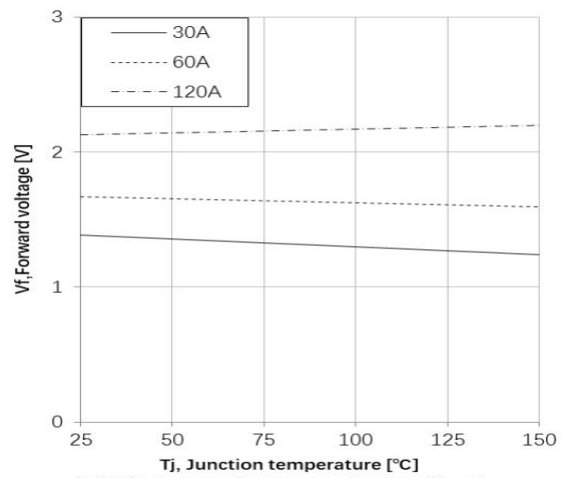
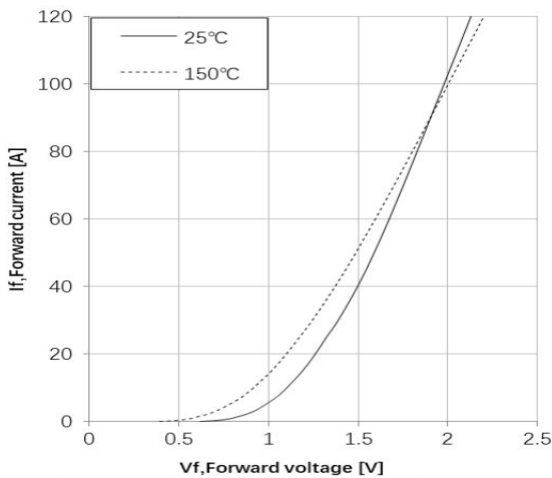
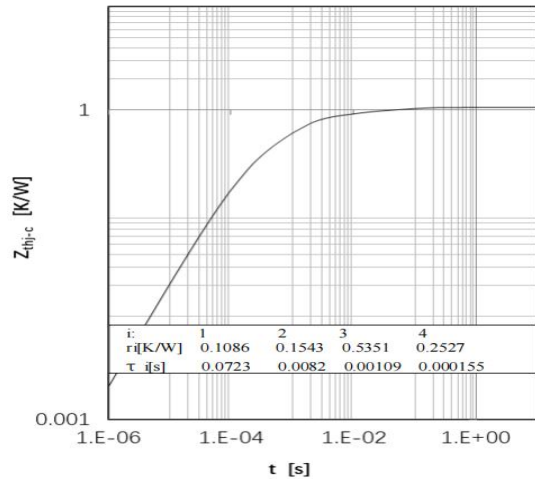
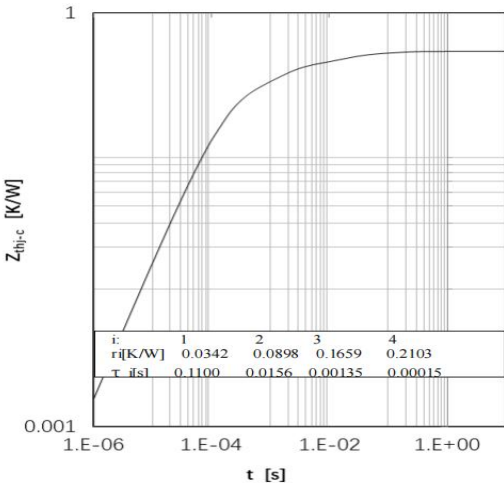
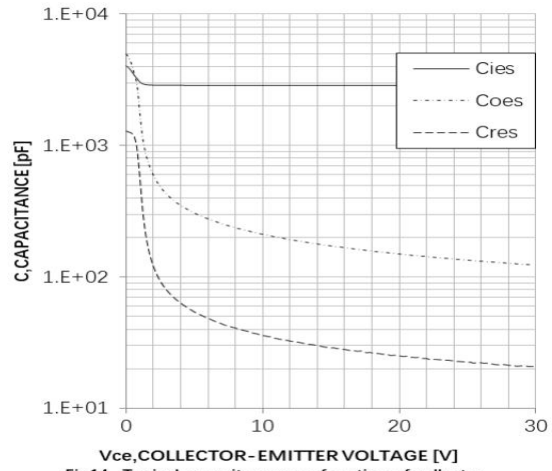
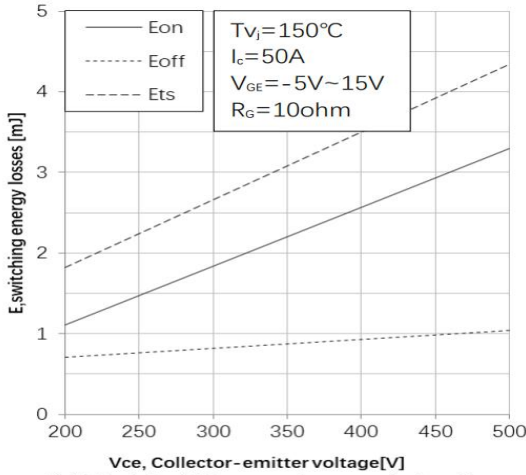


Fig6. Typical collector-emitter saturation voltage as a function of junction temperature ($V_{ge} = 15\text{V}$)

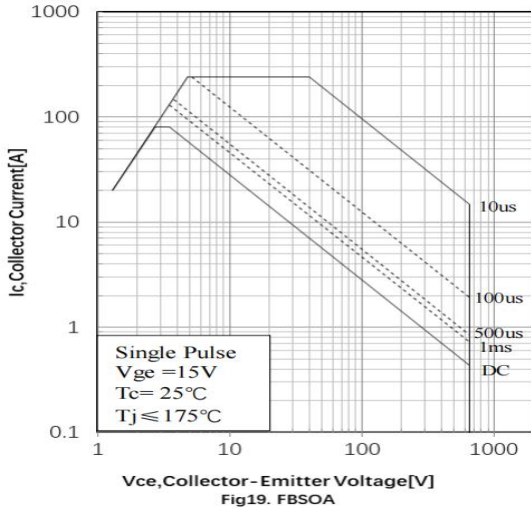
Typical Characteristics



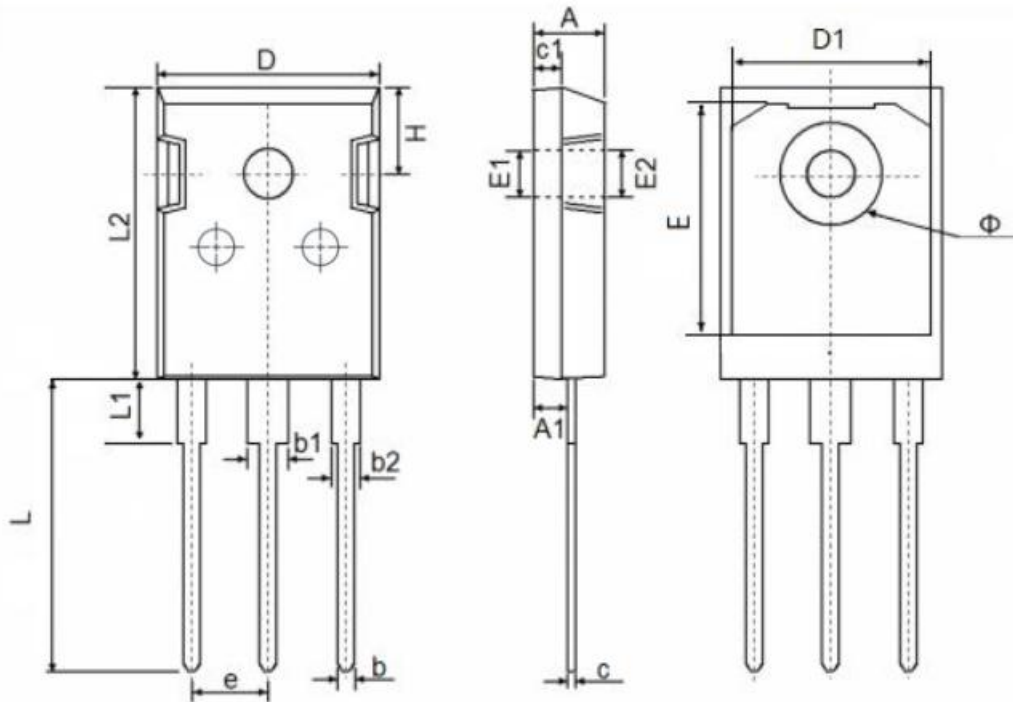
Typical Characteristics



Typical Characteristics



TO-247AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.800	5.250	0.189	0.207
A1	2.100	2.600	0.083	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.400	0.110	0.134
b2	1.800	2.420	0.071	0.095
c	0.500	0.700	0.020	0.028
c1	1.500	2.500	0.059	0.098
D	15.500	16.200	0.610	0.638
D1	13.000	14.200	0.512	0.559
E	16.250	17.650	0.640	0.695
E1	3.650	5.500	0.144	0.220
E2	3.650	5.500	0.144	0.220
L	19.400	20.400	0.764	0.803
L1	3.900	4.500	0.154	0.177
L2	20.800	21.300	0.819	0.836
φ	7.190 REF.		0.283 REF.	
e	5.440 BSC		0.214 BSC	
H	5.300	6.300	0.209	0.248